MANAGEMENT SERVICE



An ISO/TS 16949, ISO 9001 and ISO 14001 Certified Company

SILICON PLANAR POWER TRANSISTORS



2N3055 NPN MJ2955 PNP

TO-3 Metal Can Package

General Purpose Switching and Amplifier Applications

ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	VALUE	UNITS
Collector Base Voltage	V_{CBO}	100	V
Collector Emitter Voltage	V_{CEO}	60	V
Collector Emitter Voltage(R _{BE} =100Ω)	V_{CER}	70	V
Emitter Base Voltage	V_{EBO}	7	V
Collector Current Continuous	I _C	15	A
Base Current	I _B	7	A
Power Dissipation @ T _c =25°C	P _{tot}	115	W
Derate Above 25°C		0.657	W/°C
Operating And Storage Junction	T _j , T _{stg}	- 65 to +200	°C
Temperature Range			

THERMAL RESISTANCE

Junction to Case	R _{th(j-c)}	1.52	°C/W
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ELECTRICAL CHARACTERISTICS (T_C=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNITS
Collector Emitter Sustaing Voltage	$V_{CEO(sus)}^*$	I_C =200mA, I_B =0	60		V
Collector Emitter Sustaing Voltage	$V_{CER(sus)}^*$	I_C =200mA, R_{BE} =100 Ω	70		V
Collector Cut Off Current	PEX	V _{CE} =100V, V _{BE} =(off)=1.5V		1.0	mA
		T _c =150°C			
		V _{CE} =100V, V _{BE} =(off)=1.5V		5.0	
Collector Cut Off Current	ρεο	V_{CE} =30V, I_{B} =0		0.7	mA
Emitter Cut Off Current	Eво	V_{BE} =7V, I_{C} =0		5.0	mA
Collector Emitter Saturation Voltage	V _{CE(Sat)} *	I _C =4A, I _B =400mA		1.1	V
		I _C =10A, I _B =3.3A		3.0	
Base Emitter on Voltage	V _{BE(on)} *	I_C =4A, V_{CE} =4V		1.5	V
DC Current Gain	h _{FE} *	$I_C=4A, V_{CE}=4V$ 20		70	
		I _C =10A, V _{CE} =4V	5		

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ELECTRICAL CHARACTERISTICS (T_C=25°C unless specified otherwise)

Second Breakdown

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNITS
Second Breakdown Collector Current	I _S /b	V _{CE} =40V,t=1.0 s,Nonrepetitive	2.87		Α
with Base Forward Biased					

Dynamic Characteristics

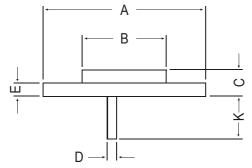
Current Gain - Bandwidth Product	f_T	I _C =0.5A, V _{CE} =10V, f=1MHz	2.5		MHz
Small Signal Current Gain	h _{fe}	I _C =1A, V _{CE} =4V, f=1KHz	15	120	
Small Signal Current Gain Cutoff	^f h _{fe}	I _C =1A, V _{CE} =4V, f=1KHz	10		KHz
Frequency					

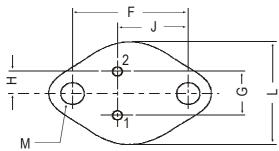
^{*}Pulse Test: Pulse Width ≤300µs, Duty Cycle ≤2%

TO-3 Metal Can Package

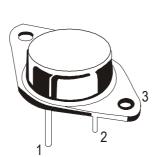
TO-3 Metal Can Package

All dimensions in mm.





DIM	MIN.	MAX.
Α	_	39.37
В	_	22.22
С	6.35	8.50
D	0.96	1.09
Е		1.77
F	29.90	30.40
G	10.69	11.18
Н	5.20	5.72
J	16.64	17.15
K	11.15	12.25
L		26.67
М	3.84	4.19



PIN CONFIGURATION

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
T0-3	100 pcs/pkt	1.3 kg/100 pcs	12.5" x 8" x 1.8"	0.1K	17" x 11.5" x 21"	2K	27.5 kgs

Notes

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TO-3
Metal Can Package

Disclaimer

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Continental Device India Limited

C-120 Naraina Industrial Area, New Delhi 110 028, India.

Telephone + 91-11-2579 6150, 5141 1112 Fax + 91-11-2579 5290, 5141 1119 email@cdil.com www.cdilsemi.com

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